Abstracts

High efficiency 0.4 /spl mu/m gate LDMOS power FET for low voltage wireless communications

G. Ma, W. Burger and M. Shields. "High efficiency 0.4 /spl mu/m gate LDMOS power FET for low voltage wireless communications." 1999 MTT-S International Microwave Symposium Digest 99.3 (1999 Vol. III [MWSYM]): 1195-1198 vol.3.

A low cost, high efficiency 4th generation silicon MOSFET using RFLDMOS (LV4) 0.4 /spl mu/m technology is presented which has been developed for high frequency (1-2 GHz) and low voltage (2.2-12.5 V) applications. Key results include 78% PAE at 31.8 dBm for 3.6 V, 900 MHz AMPS applications, and 63% PAE, 12.5 dB gain, 30.5 dBm for 2.4 V, 900 MHz for 2-way paging applications.

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